

High Power Single Emitter Diode Lasers, 808nm, 12W CW



Features:

- High output power
- High electrical-optical conversion efficiency
- High brightness
- High reliability

Technical Advantages:

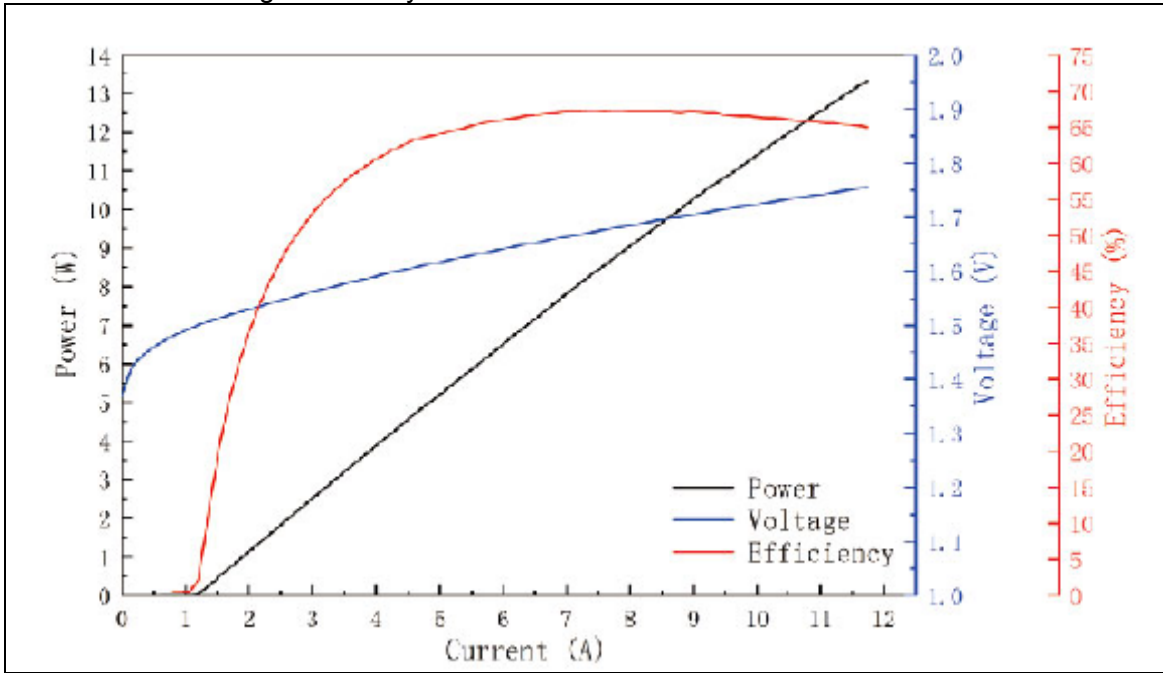
- High efficient epitaxial structure design
- High-quality epitaxial material growth
- Special passivation method for cavity surface

Specifications

	Symbol	Min.	Typical	Max.	Unit
Operation					
Optical output power	P _o		12		W
Wavelength	λ _o	806	808	811	nm
Operation mode			CW		
Dimensions					
Emission region width	E.W.	185	190	195	um
Cavity length	L	3980	4000	4020	um
Width	W	480	500	520	um
Thickness	D	115	120	125	um
Electro-optical parameters					
Electro-optical efficiency	η	62	65		%
Slope efficiency	SE	1.2	1.3		W/A
Threshold efficiency	l _{th}		1.3	1.4	A
Operation current	I _{op}		10.5	11	A
Operation voltage	V _{op}		1.75	1.8	V
Spectral width FWHM	Δλ		2	3	nm
Wavelength shift vs. temp.	Δλ/ΔT		0.3		Nm/°C
Vertical far field divergence angle	θ _⊥		32	35	Deg
Horizontal far field divergence angle	θ _∥		6	8	Deg
Polarization	TE	95			%

Remark: Tested with COS packaged products in the CW mode at 25 °C.

Current-Power-Voltage-Efficiency



Spectral Characteristics

